PRODUCT ADVISORY

Corrections to Standard Microcircuit Drawing 5962-95689 for Intersil Products HS0-26C32RH-Q and HS0-26CLV32RH-Q

Refer to:
PA13002

Date: January 4, 2013

January 4, 2013

To: Our Valued Intersil Customers

Subject: **Corrections to Standard Microcircuit Drawing 5962-95689 for Intersil Products HS0-26C32RH-Q and HS0-26CLV32RH-Q**

This advisory is to inform you that Intersil has made corrections to DLA (Defense Logistics Agency) Land and Maritime SMD (Standard Microcircuit Drawing) 5962-95689 for the HS0-26C32RH-Q and HS0-26CLV32RH-Q products. The updates correct errors in the die dimensions as specified under Figure A-1 of Appendix A. There have been no changes to the die/silicon or product itself. The updated SMD is available on the DLA website at http://www.landandmaritime.dla.mil/Downloads/MilSpec/Smd/95689.pdf.

Products affected:

Intersil Part Number	DLA SMD Part Number
HS0-26C32RH-Q	5962F9568901V9A
HS0-26CLV32RH-Q	5962F9568902V9A

Intersil will take all necessary actions to conform to agreed upon customer requirements and to ensure the continued high quality and reliability of Intersil products being supplied. Customers may expect to continue receiving product processed to the same established conditions and systems used for manufacturing of material supplied today.

If you have concerns with this advisory, Intersil must hear from you promptly. Please contact the nearest Intersil Sales Office or call the Intersil Corporate line at 1-888-468-3774, in the United States, or 1-321-724-7143 outside of the United States.

Regards,

Jon Brewster
Intersil Corporation

PA13002

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PA13002 – Figure A-1 Updates

From:

Die physical dimensions.
Die size: 2140 x 3290 microns
Die thickness: 21 ± 1 mils

Interface materials.
Top metallization: Si Al Cu 10.0 kÅ ± 1 kÅ
Backside metallization: None: chemical etch

Glassivation.
Type: PSG
Thickness: 8 kÅ ± 1 kÅ

Substrate: Single crystal silicon

Assembly related information.
Substrate potential: substrate internally tied to V_{DD}
Special assembly instructions: None

To:

Die physical dimensions.
Die size: 1970 x 3120 microns
Die thickness: 21 ± 1 mils

Interface materials.
Top metallization: Si Al Cu 10.0 kÅ ± 1 kÅ
Backside metallization: None: chemical etch

Glassivation.
Type: PSG
Thickness: 8 kÅ ± 1 kÅ

Substrate: Single crystal silicon

Assembly related information.
Substrate potential: substrate internally tied to V_{DD}
Special assembly instructions: None